EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	7	((HITOSHI) near2 (ISHIZAKA)).INV.	USPAT	OR	ON	2008/12/05 09:53
S2	66	((HITOSHI) near2 (ISHIZAKA)).INV.	EPO; JPO; DERWENT	OR	ON	2008/12/05 09:54
S3	8	((DAISUKE) near2 (UENDA)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 09:56
S4	47	((DAISUKE) near2 (UENDA)).INV.	EPO; JPO; DERWENT	OR	ON	2008/12/05 09:57
S5	4	((DAISUKE) near2 (HANAI)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 09:59
S6	20	((DAISUKE) near2 (HANAI)).INV.	EPO; JPO; DERWENT	OR	ON	2008/12/05 09:59
S7	1682	(134/6).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/12/05 09:59
S8	8	(polyamic adj acid) same semiconductor same clean $4	US-PGPUB; USPAT	OR	ON	2008/12/05 10:00
S9	426	(poly(amic) adj acid) same semiconductor same clean$4	US-PGPUB; USPAT	OR	ON	2008/12/05 10:01
S10	7	(poly near2 acid) same semiconductor with clean $4	US-PGPUB; USPAT	OR	ON	2008/12/05 10:01
S11	580	S7 and (semiconductor or varnish or resin)	US-PGPUB; USPAT	OR	ON	2008/12/05 10:02
S12	3	(clean$4 near2 (member or tool or device)) near6 wafer near6 resin	US-PGPUB; USPAT	OR	ON	2008/12/05 10:05
S13	4	(clean$4 near2 (member or tool or device)) near6 wafer near6 resin	EPO; JPO; DERWENT	OR	ON	2008/12/05 10:05
S14	78	(varnish or resin or polyamic) near5 wafer same clean$5	EPO; JPO; DERWENT	OR	ON	2008/12/05 10:07
S15	0	("2007/0163621").URPN.	USPAT	OR	ON	2008/12/05 11:21
S16	2	"cleaning member" near5 ((heat$1resistant or "heat resistant") near2 resin)	USPAT	OR	ON	2008/12/05 11:26
S17	81	clean$$ same ((heat $1resistant or "heat resistant") near3 resin)	USPAT	OR	ON	2008/12/05 11:27

S18	114	clean$$ same ((heat $1resistant or "heat resistant") near3 resin)	EPO; JPO; DERWENT	OR	ON	2008/12/05 11:29
S19	102	(clean$4 near2 member) with semiconductor	EPO; JPO; DERWENT	OR	ON	2008/12/05 11:33
S20	13	US-5911837-$.DID. OR US-6357142-$.DID. OR US-6492284-$.DID. OR US-6502591-$.DID. OR US-6511914-$.DID. OR US-6774056-$.DID. OR US-6875284-$.DID.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	ON	2008/12/05 11:59
S21	1	("20060105164").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/05 12:54
S22	2	("20060105164").PN.	US-PGPUB; USPAT; DERWENT	OR	OFF	2008/12/05 12:54
S23	0	("2006/0105164").URPN.	USPAT	OR	ON	2008/12/05 12:55
S24	101	namikawa.in.	USPAT	OR	ON	2008/12/05 12:55
S25	1	("20030136430").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/05 13:00
S26	1	("20050244632").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/05 13:02
S27	1569	clean$4 near3 (sheet or member) same (resin or polyamic)	US-PGPUB; USPAT	OR	ON	2008/12/05 13:30
S28	758	clean$4 near3 (sheet or member) with (resin or polyamic)	US-PGPUB; USPAT	OR	ON	2008/12/05 13:30
S29	44	clean$4 near3 (sheet or member) with (resin or polyamic) same (semiconductor or wafer)	US-PGPUB; USPAT	OR	ON	2008/12/05 13:31
S30	44	clean$4 near3 (sheet or member) with (resin) same (semiconductor or wafer)	US-PGPUB; USPAT	OR	ON	2008/12/05 13:32
S31	10	"heat-resistant resin" same polyimide same clean$$	US-PGPUB; USPAT	OR	ON	2008/12/05 13:34
S32	32	"heat resistant resin" same polyimide same clean$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/12/05 13:36
S33	1	("20040204334").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/05 13:39

S34	2	("20040204334").PN.	US-PGPUB; USPAT; DERWENT	OR	OFF	2008/12/05 13:39
S35	1671	(156/344).CCLS.	US-PGPUB; USPAT; DERWENT	OR	OFF	2008/12/05 13:55
S36	153	S35 and resist	US-PGPUB; USPAT	OR	ON	2008/12/05 13:55
S37	1339	"polyimide film" same semiconductor	EPO; JPO; DERWENT	OR	ON	2008/12/05 14:15
S38	955	"polyimide film" with semiconductor	EPO; JPO; DERWENT	OR	ON	2008/12/05 14:15
S39	4	"polyimide film" with semiconductor with clean $4	EPO; JPO; DERWENT	OR	ON	2008/12/05 14:15
S40	5	(("5395803") or ("5902399") or ("6716478") or ("6884294") or ("6960540")).PN.	US-PGPUB; USPAT	OR	OFF	2008/12/08 10:06
S41	1425	(427/240).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/12/08 10:09
S42	714	S41 and (spin near2 coat $4)	US-PGPUB; USPAT	OR	ON	2008/12/08 10:10
S43	15	S41 and ((spin near2 coat $4) same uncoat$4)	US-PGPUB; USPAT	OR	ON	2008/12/08 10:10
S44	20	S41 and ((spin near2 coat $4) same spiral)	US-PGPUB; USPAT	OR	ON	2008/12/08 10:11
S45	519	(427/271).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/12/08 10:13
S46	370	S45 and remov$4	US-PGPUB; USPAT	OR	ON	2008/12/08 10:14
S47	26	(clean$4 near2 (member or head)) with coat$4 with expos$4	US-PGPUB; USPAT	OR	ON	2008/12/08 11:36
S48	1	("20030136430").PN.	US-PGPUB; USPAT	OR	OFF	2008/12/08 11:45
S49	0	("2003/0136430").URPN.	USPAT	OR	ON	2008/12/08 11:45
S50	5591	(134/6,42,902).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/12/08 12:53
S51	22	S50 and (clean$4 with wafer with (resin or varnish))	US-PGPUB; USPAT	OR	ON	2008/12/08 12:54
S52	1682	(134/6).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/12/08 13:04
S53	241	S52 and (clean$4 near8 member)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:04

S54	203	S52 and (clean$4 near4 member)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:04
S55	21	S52 and ((clean$4 near4 member) same wafer)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:05
S56	0	("2005/0118414").URPN.	USPAT	OR	ON	2008/12/08 13:05
S57	2	("20050118414").PN.	US-PGPUB; USPAT; DERWENT	OR	OFF	2008/12/08 13:13
S58	39622	(varnish or resin or coating) same (dri$3 or drying) same (cure or curing or cured)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:25
S59	17690	(varnish or resin or coating) with (dri$3 or drying) with (cure or curing or cured)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:25
S60	8032	S59 and ("134".clas. or "118".clas. or "428".clas. or "427".clas.)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:26
S61	770	S60 and (wafer or semiconductor)	US-PGPUB; USPAT	OR	ON	2008/12/08 13:26
S62	312	S61 and clean$4	US-PGPUB; USPAT	OR	ON	2008/12/08 13:27
S63	2	"cleaning layer" with wafer with expos$4	US-PGPUB; USPAT	OR	ON	2008/12/08 14:03
S64	2	("20040204334").PN.	US-PGPUB; USPAT; DERWENT	OR	OFF	2008/12/08 14:04
S65	635	edge near2 bead near2 removal	US-PGPUB; USPAT	OR	ON	2008/12/08 14:24
S66	6	("cleaning member" or wafer) with ((mark$4 near3 lot near2 manag$5) or indentif$5)	US-PGPUB; USPAT	OR	ON	2008/12/08 14:43
S67	0	("cleaning member" or wafer) with ((mark$4 near3 lot near2 manag$5) or indentif$5)	JPO	OR	ON	2008/12/08 14:43
S68	9	("cleaning member" or wafer) with ((lot near2 manag$5) or indentif$5)	JPO	OR	ON	2008/12/08 14:43
S69	125	("cleaning member" or wafer) with ((lot near2 manag$5) or indentif$5)	US-PGPUB; USPAT; DERWENT	OR	ON	2008/12/08 14:44
S70	4	("cleaning member" or wafer) with ((lot near2 manag$5) or indentif$5) same clean$4	US-PGPUB; USPAT; DERWENT	OR	ON	2008/12/08 14:45

S71	0	"cleaning member" with wafer with (surface near3 expos$4)	EPO; JPO; DERWENT	OR	ON	2008/12/08 14:45
S72	111	clean$4 with wafer with (surface near3 expos$4)	EPO; JPO; DERWENT	OR	ON	2008/12/08 14:46
S73	2	"cleaning member" with wafer with coat$5	EPO; JPO; DERWENT	OR	ON	2008/12/08 14:50
S74	97	clean$4 with wafer with coat$5 with remov$5	EPO; JPO; DERWENT	OR	ON	2008/12/08 14:51
S75	95	(clean$4 with (member or layer)) with wafer with expos$4	EPO; JPO; DERWENT	OR	ON	2008/12/08 15:22
S76	69	(clean$4 with (member or layer)) with wafer near8 expos$4	EPO; JPO; DERWENT	OR	ON	2008/12/08 15:22
S77	1876	wafer with (area or circumference or circle or edge) with coat$4 with (remov$4 or uncoat$4 or expos$4)	US-PGPUB; USPAT	OR	ON	2008/12/08 15:54
S78	236	(semiconductor near2 wafer) with (area or circumference or circle or edge) with coat$4 with (remov$4 or uncoat$4 or expos$4)	US-PGPUB; USPAT	OR	ON	2008/12/08 15:55

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